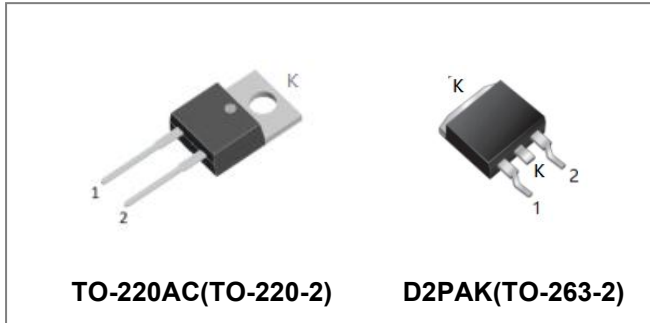


## S3D12065A S3D12065G 650V SiC POWER SCHOTTKY RECTIFIERS



### Description

S3D12065A/S3D12065G are SiC Schottky rectifiers packaged in TO-220AC(TO-220-2)/D2PAK(TO-263-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D12065A/S3D12065G are ideal for energy sensitive, high frequency applications in challenging environments.

### Circuit Diagram



### Features

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

### Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	650	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>DC</sub>			
Average Rectified Forward Current	I <sub>F(AV)1</sub>	@T <sub>c</sub> =25°C	24	A
	I <sub>F(AV)2</sub>	@T <sub>c</sub> =157°C	12	A
Repetitive Peak Forward Surge Current	I <sub>FRM1</sub>	10ms, Half Sine pulse, T <sub>c</sub> =25°C	60	A
	I <sub>FRM2</sub>	10ms, Half Sine pulse, T <sub>c</sub> =110°C	40	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM1</sub>	10ms, Half Sine pulse, T <sub>c</sub> =25°C	140	A
	I <sub>FSM2</sub>	10ms, Half Sine pulse, T <sub>c</sub> =110°C	96	A
Non-Repetitive Peak Forward Surge Current	I <sub>F,Max1</sub>	10µs. Pulse, T <sub>c</sub> =25°C	1200	A
	I <sub>F,Max2</sub>	10µs. Pulse, T <sub>c</sub> =110°C	100	A
Power Dissipation	P <sub>tot1</sub>	T <sub>c</sub> =25°C	143	W
	P <sub>tot2</sub>	T <sub>c</sub> =110°C	62	W

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 12A, Pulse, T <sub>J</sub> = 25 °C	1.5	1.7	V
	V <sub>F2</sub>	@ 12A, Pulse, T <sub>J</sub> = 175 °C	1.75	2.2	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.1	6	uA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 175 °C	1.5	50	uA
Junction Capacitance	C <sub>T</sub>	V <sub>R</sub> =0V, T <sub>J</sub> =25°C, f=1MHz	764	-	pF
Reverse Recovery Charge	Q <sub>c</sub>	I <sub>F</sub> = 12A, di/dt = 200A/μs V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	84.07	-	nC
Capacitance Stored Energy	E <sub>c</sub>	V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	17.30	-	μJ

\* Pulse width < 300 μs, duty cycle < 2%

### Thermal-Mechanical Specifications:

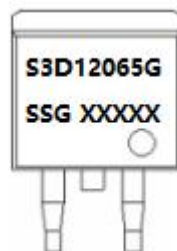
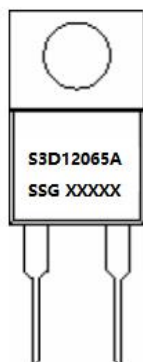
Characteristics	Symbol	S3D12065A	S3D12065G	Units
Junction Temperature	T <sub>J</sub>	-55 to +175		°C
Storage Temperature	T <sub>stg</sub>	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	1.05	1.01	°C/W

### Ordering Information

Device	Package	Shipping
S3D12065A	TO-220AC(TO-220-2)	50pcs / tube
S3D12065G	D2PAK(TO-263-2)	800pcs /Reel
S3D12065GTR	D2PAK(TO-263-2)	800pcs /Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Marking Diagram



Where XXXXX is YYWWL

S3D = Device Type  
A/G = Package type  
12 = Forward Current (12A)  
065 = Reverse Voltage (650V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Ratings and Characteristics Curves

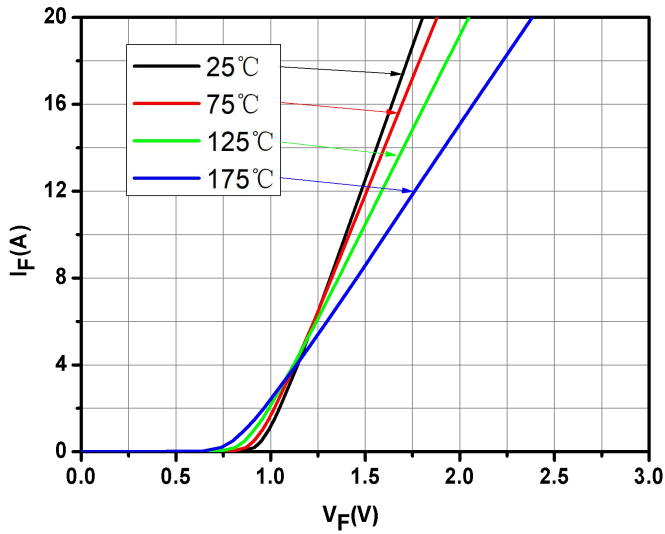


Fig.1-Typical Forward Voltage Characteristics

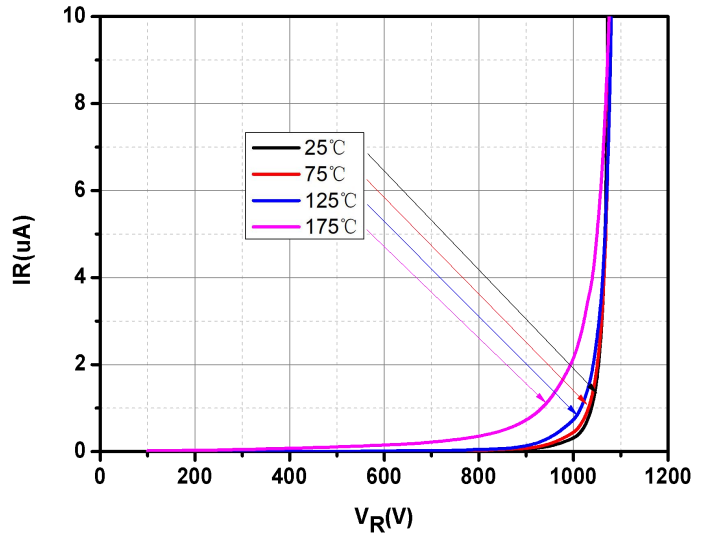


Fig.2-Typical Reverse Characteristics

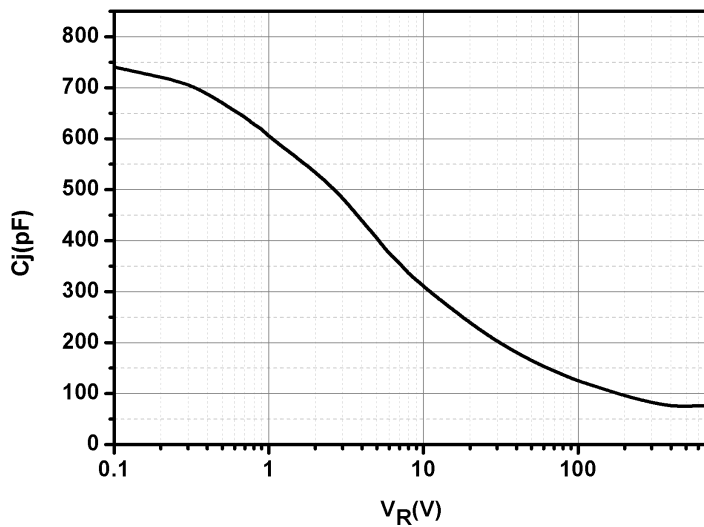


Fig.3-Capacitance vs. Reverse Voltage

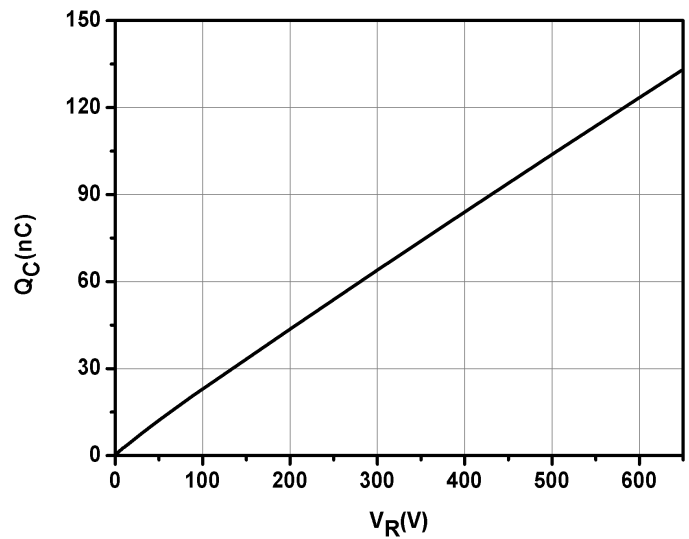


Fig.4-Total Capacitance Charge vs. Reverse Voltage

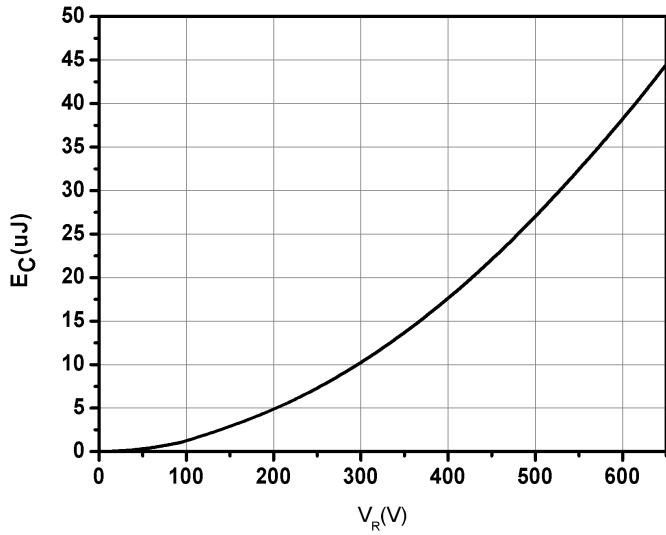


Fig.5-Capacitance Stored Energy

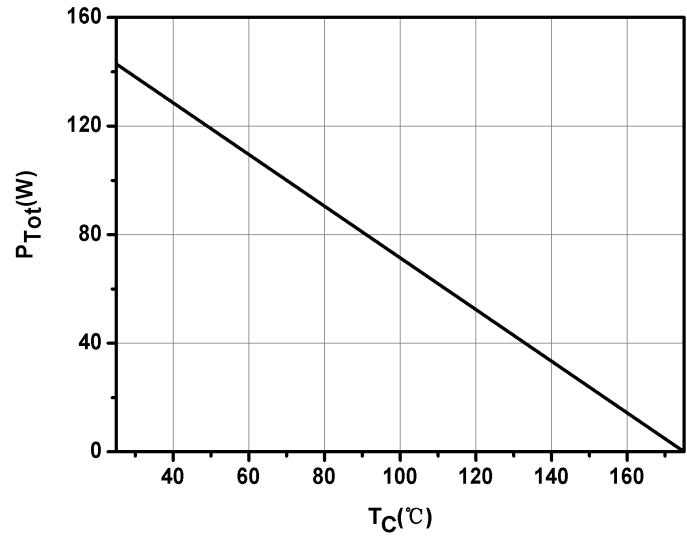


Fig.6-Power Derating

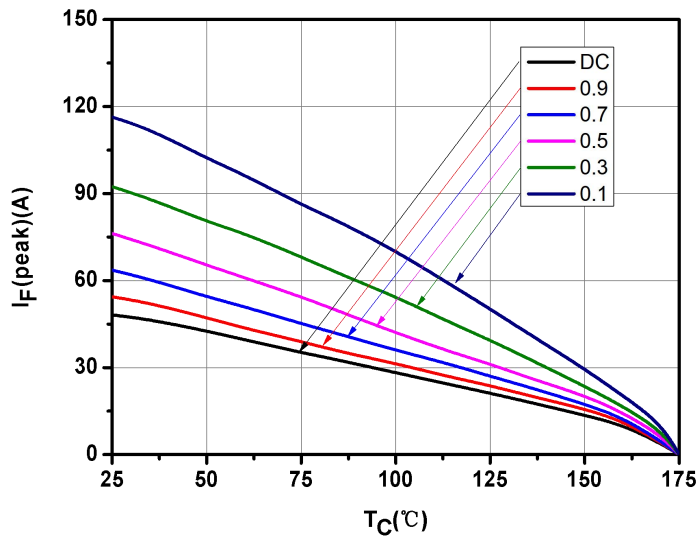
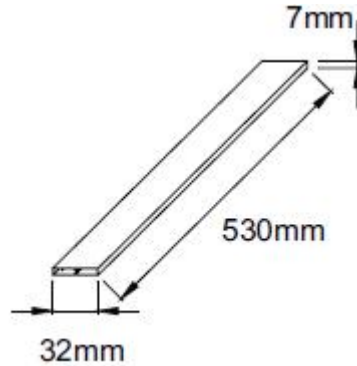
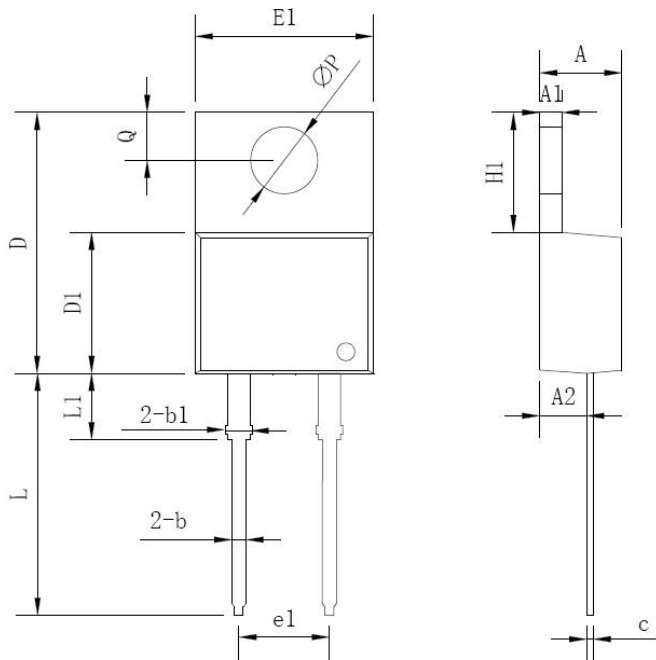


Fig.7-Current Derating

### Tube Specification(TO-220-2)

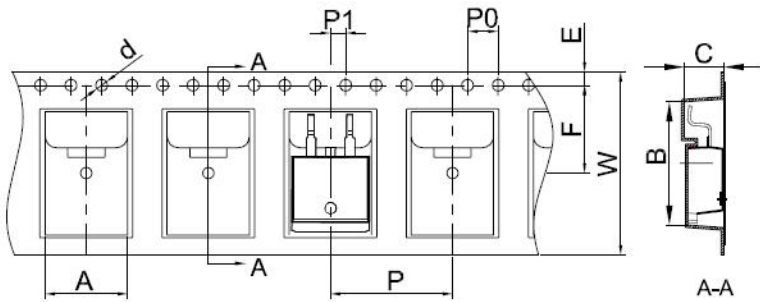


### Mechanical Dimensions TO-220AC(TO-220-2)



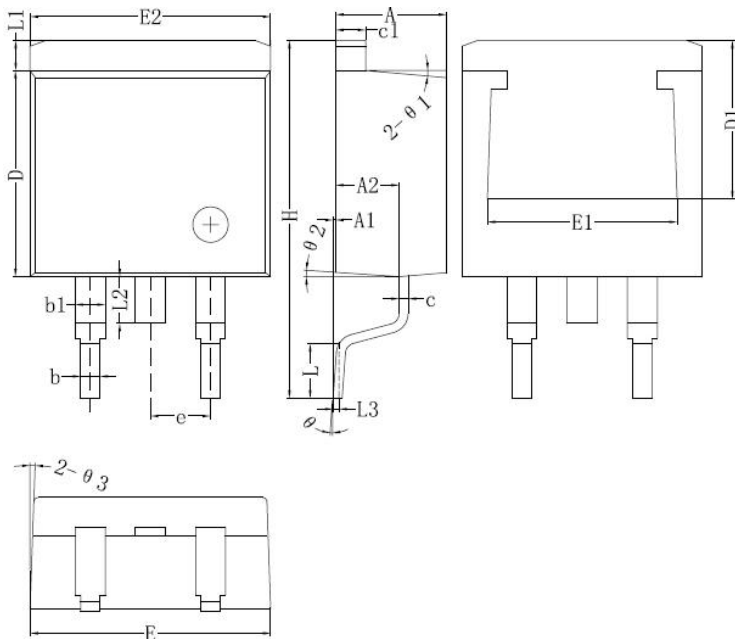
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
ΦP	-	3.56	-
Q	2.54	-	3.43

**Carrier Tape & Reel Specification D2PAK(TO-263-2)**



SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

**Mechanical Dimensions D2PAK(TO-263-2)**



Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	8.65
D1	6.40	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.60	15.88
L	1.78	2.80
L1	-	1.68
L2	-	2.2
L3	0.255BSC	
θ	0	8°



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